# N-Channel 30-V (D-S) MOSFET

# **Key Features:**

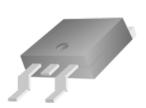
- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

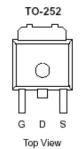
<b>Typical</b>	Αp	plica	ition	s:
. ,				

- · Automotive Systems
- DC/DC Conversion Circuits
- Battery Powered Power Tools

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I⊳ (A)		
30	$3.9 @ V_{GS} = 10V$	93		







ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)					
Parameter			Limit	Units	
Drain-Source Voltage			30	V	
Gate-Source Voltage			±20	V	
Continuous Drain Current a	T <sub>C</sub> =25°C	$I_D$	93	Α	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	350	^	
Continuous Source Current (Diode Conduction) <sup>a</sup>			93	Α	
Power Dissipation <sup>a</sup>	T <sub>C</sub> =25°C	$P_{D}$	50	W	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient <sup>a</sup>	$R_{\theta JA}$	40	°C/W		
Maximum Junction-to-Case	$R_{\theta JC}$	3	C/VV		

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#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

### **Electrical Characteristics**

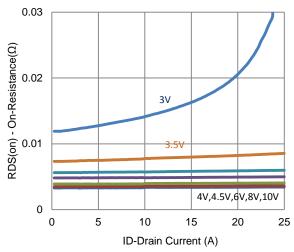
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \text{ uA}$	1			V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1 uA	
Zero Gate Voltage Brain Garrent	יטאי	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	u/ t
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	130			Α
Drain-Source On-Resistance a	r <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$			3.9	mΩ
Forward Transconductance a	$g_{fs}$	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		11		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 45 \text{ A}, V_{GS} = 0 \text{ V}$		0.75		V
		Dynamic <sup>b</sup>				
Total Gate Charge	$Q_g$	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$		36		
Gate-Source Charge	$Q_gs$	$I_{D} = 20 \text{ A}$		12		nC
Gate-Drain Charge	$Q_gd$	1 <sub>0</sub> = 23 / 1		13		
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = 15 \text{ V}, R_{L} = 0.8 \Omega,$		12		
Rise Time	t <sub>r</sub>	$I_{DS} = 10 \text{ V}, R_{L} = 0.0 \Omega_{2},$ $I_{D} = 20 \text{ A},$		15		ns
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		89		113
Fall Time	t <sub>f</sub>	GEN - 10 V, NGEN 0 12		30		
Input Capacitance	C <sub>iss</sub>			6725		
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		466		pF
Reverse Transfer Capacitance	$C_{rss}$			397		

#### Notes

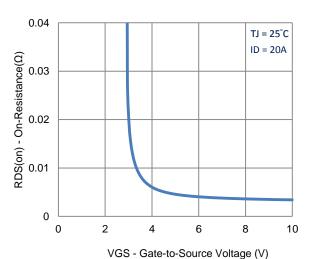
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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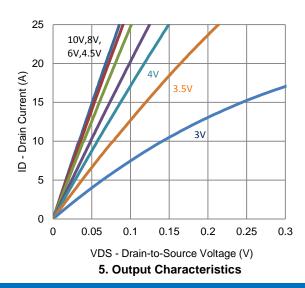
## **Typical Electrical Characteristics**

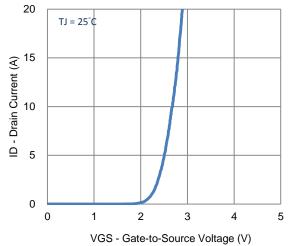


#### 1. On-Resistance vs. Drain Current

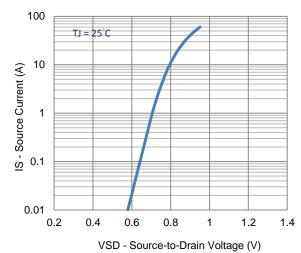


3. On-Resistance vs. Gate-to-Source Voltage

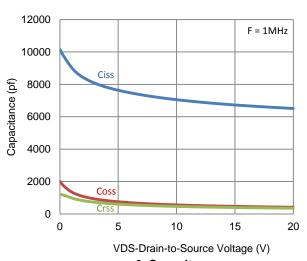




2. Transfer Characteristics

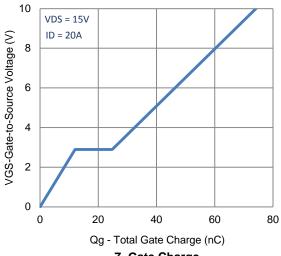


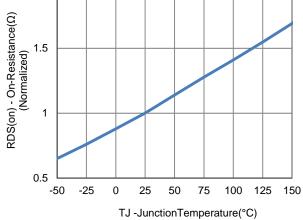
4. Drain-to-Source Forward Voltage



## **Typical Electrical Characteristics**

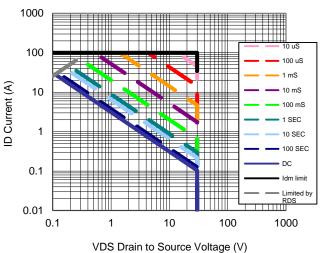
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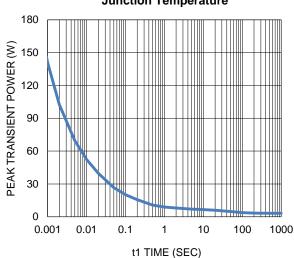




7. Gate Charge

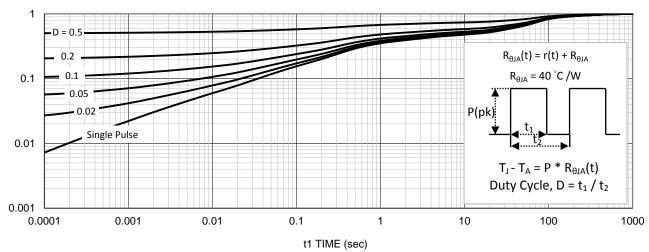






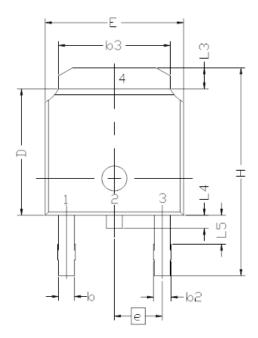
9. Safe Operating Area

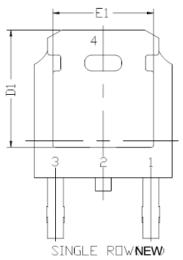
10. Single Pulse Maximum Power Dissipation

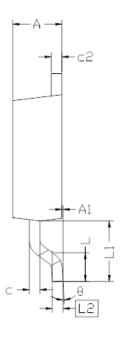


11. Normalized Thermal Transient Junction to Ambient

### **Package Information**







	DIMENS:	[DNAL	REQMTS
SYMBOL	MIN	NDM	MAX
E	6.40	6.60	6.731
L	1.40	1.52	1.77
L1		.743 R	
L2	0.	.508 BS	_
L3	0.89		1.27
L4	0.64		1.01
L5			
D	6.00	6.10	6,223
Н	9.40	10.00	10.40
b	0.64	0.76	0,88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
е		286 BS	
Α	2,20	2.30	2,38
A1	0		0.127
C	0.45	0.50	0.60
c2	0.45	0,50	0.58
D1	5,30		
E1	4.40		
θ	0°		10°

### Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.